# **BGA2865**

### **MMIC** wideband amplifier

Rev. 2 — 1 November 2010

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

Silicon Monolithic Microwave Integrated Circuit (MMIC) wideband amplifier with internal matching circuit in a 6-pin SOT363 plastic SMD package.

#### 1.2 Features

- Input internally matched to 50  $\Omega$
- A gain of 32.2 dB at 950 MHz
- Output power at 1 dB gain compression = 8 dBm
- Supply current = 29.9 mA at a supply voltage of 5 V
- Reverse isolation > 34 dB up to 2 GHz
- Good linearity with low second order and third order products
- Noise figure = 3.9 dB at 950 MHz
- Unconditionally stable (K > 1)
- No output inductor required

#### 1.3 Applications

- LNB IF amplifiers
- General purpose low noise wideband amplifier for frequencies between DC and 2.2 GHz

## 2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	$V_{CC}$	D. D. D.	
2, 5	GND2	654	$\sim$
3	RF_OUT		6— >—3
4	GND1	0	4 2,5
6	RF_IN	∐1 ∐2 ∐3	4   12, 3 777 777 sym052



#### **MMIC** wideband amplifier

## 3. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BGA2865	-	plastic surface-mounted package; 6 leads	SOT363

### 4. Marking

Table 3. Marking

Type number	Marking code	Description
BGA2865	*EC	* = - : made in Hong Kong
		* = p : made in Hong Kong
		* = W : made in China
		* = t : made in Malaysia

## 5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage	RF input AC coupled	-0.5	5.5	V
I <sub>CC</sub>	supply current		-	36	mA
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 90 °C	-	200	mW
T <sub>stg</sub>	storage temperature		-40	+125	°C
Tj	junction temperature		-	125	°C
P <sub>drive</sub>	drive power		-	-21	dBm

#### 6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j\text{-sp})}$	thermal resistance from junction to solder point	$P_{tot} = 200 \text{ mW}; T_{sp} = 90 ^{\circ}\text{C}$	300	K/W

#### 7. Characteristics

Table 6. Characteristics

 $V_{CC} = 5.0 \text{ V; } Z_S = Z_L = 50 \Omega; P_i = -35 \text{ dBm; } T_{amb} = 25 \text{ °C; } measured on demo board; } unless otherwise specified.$ 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CC}$	supply voltage		4.5	5.0	5.5	V
Icc	supply current		23.0	26.4	29.7	mΑ

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### **MMIC** wideband amplifier

**Table 6.** Characteristics ...continued  $V_{CC} = 5.0 \text{ V}; Z_S = Z_L = 50 \Omega; P_i = -35 \text{ dBm}; T_{amb} = 25 ^{\circ}\text{C}; measured on demo board; unless otherwise specified.$ 

	, 1, _3 _L 00 12, 1 00 02, 1 allib	20 0,		0,000	·	
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	f = 250 MHz	30.3	30.9	31.5	dB
		f = 950 MHz	31.5	32.2	32.9	dB
		f = 2150 MHz	28.1	29.6	31.1	dB
RLin	input return loss	f = 250 MHz	14	16	18	dB
		f = 950 MHz	17	18	20	dB
		f = 2150 MHz	10	11	18	dB
RLout	output return loss	f = 250 MHz	14	18	23	dB
		f = 950 MHz	9	10	11	dB
		f = 2150 MHz	7	9	12	dB
ISL	isolation	f = 250 MHz	41	61	82	dB
		f = 950 MHz	41	43	44	dB
		f = 2150 MHz	34	37	39	dB
NF	noise figure	f = 250 MHz	3.4	3.8	4.3	dB
		f = 950 MHz	3.4	3.9	4.3	dB
		f = 2150 MHz	3.6	4.0	4.5	dB
B <sub>-3dB</sub>	-3 dB bandwidth	3 dB below gain at 1 GHz	2.1	2.2	2.4	GHz
K	Rollett stability factor	f = 250 MHz	14	16	18	
,,	f = 950 MHz	1.2	1.5	1.8		
		f = 2150 MHz	0.9	1.2	1.4	
P <sub>L(sat)</sub>	saturated output power	f = 250 MHz	10	11	12	dBm
, ,		f = 950 MHz	8	9	10	dBm
		f = 2150 MHz	2	3	5	dBm
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	f = 250 MHz	8	9	10	dBm
		f = 950 MHz	6	8	9	dBm
		f = 2150 MHz	1	2	3	dBm
IP3 <sub>I</sub>	input third-order intercept point	P <sub>drive</sub> = −38 dBm (for each tone)				
		$f_1 = 250 \text{ MHz}; f_2 = 251 \text{ MHz}$	-13	-11	-8	dBm
		$f_1 = 950 \text{ MHz}; f_2 = 951 \text{ MHz}$	-16	-14	-11	dBm
		$f_1 = 2150 \text{ MHz}; f_2 = 2151 \text{ MHz}$	-23	-20	-17	dBm
IP3 <sub>O</sub>	output third-order intercept point	P <sub>drive</sub> = −38 dBm (for each tone)				
		$f_1 = 250 \text{ MHz}; f_2 = 251 \text{ MHz}$	18	20	22	dBm
		$f_1 = 950 \text{ MHz}; f_2 = 951 \text{ MHz}$	16	19	21	dBm
		f <sub>1</sub> = 2150 MHz; f <sub>2</sub> = 2151 MHz	7	10	13	dBm
P <sub>L(2H)</sub>	second harmonic output power	P <sub>drive</sub> = −35 dBm				
		f <sub>1H</sub> = 250 MHz; f <sub>2H</sub> = 500 MHz	-52	-50	-48	dBm
		f <sub>1H</sub> = 950 MHz; f <sub>2H</sub> = 1900 MHz	-42	-40	-39	dBm
ΔIM2	second-order intermodulation distance	P <sub>drive</sub> = −38 dBm (for each tone)				
		f <sub>1</sub> = 250 MHz; f <sub>2</sub> = 251 MHz	36	47	58	dBc
		11 = 250 WI 12, 12 = 251 WI 12	30	71	00	abo

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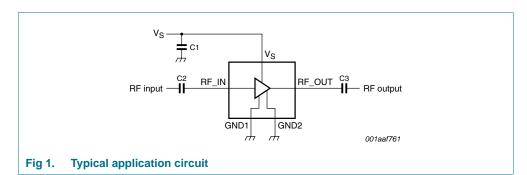
**MMIC** wideband amplifier

## 8. Application information

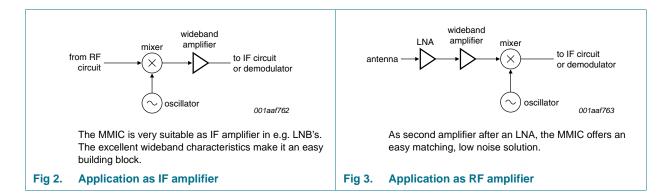
Figure 1 shows a typical application circuit for the BGA2865 MMIC. The device is internally matched to 50  $\Omega$  and therefore does not need any external matching. The value of the input and output DC blocking capacitors C2 and C3 should not be more than 100 pF for applications above 100 MHz. However, when the device is operated below 100 MHz, the capacitor value should be increased.

The 22 nF supply decoupling capacitor C1 should be located as close as possible to the MMIC.

The PCB top ground plane, connected to pins 2, 4 and 5 must be as close as possible to the MMIC, preferably also below the MMIC. When using via holes, use multiple via holes as close as possible to the MMIC.



## 8.1 Application examples



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### 8.2 Graphs

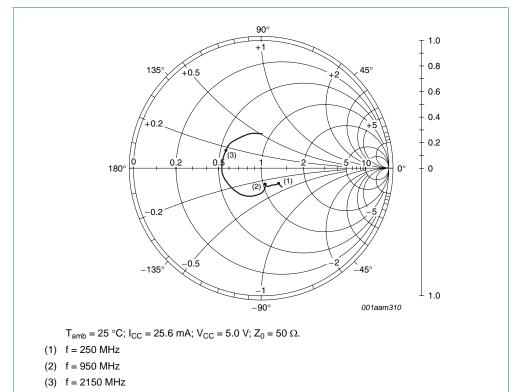
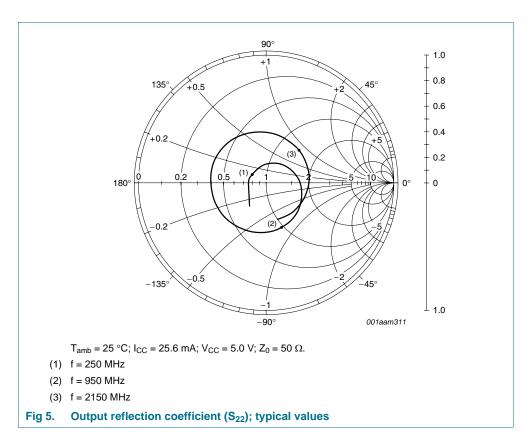
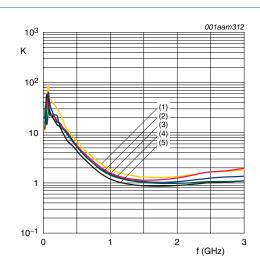


Fig 4. Input reflection coefficient (S<sub>11</sub>); typical values



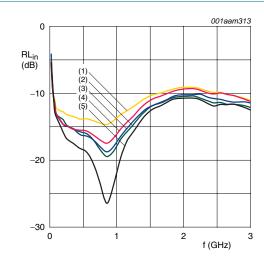
#### **MMIC** wideband amplifier



 $P_{drive} = -40 \text{ dBm}; Z_0 = 50 \Omega.$ 

- (1)  $V_{CC} = 4.5 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 21.70 \,\text{mA}$
- (2)  $V_{CC} = 4.5 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 23.82 \,\text{mA}$
- (3)  $V_{CC} = 5.0 \text{ V}$ ;  $T_{amb} = 25 \,^{\circ}\text{C}$ ;  $I_{CC} = 25.59 \,\text{mA}$
- (4)  $V_{CC} = 5.5 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 27.33 \,\text{mA}$
- (5)  $V_{CC} = 5.5 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 29.30 \,\text{mA}$

Fig 6. Rollett stability factor as function of frequency; typical values



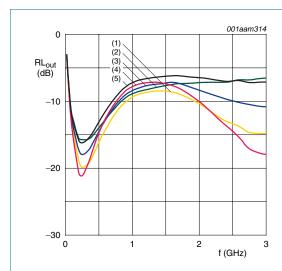
 $P_{drive} = -40 \text{ dBm}; Z_0 = 50 \Omega.$ 

- (1)  $V_{CC} = 4.5 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 21.70 \,\text{mA}$
- (2)  $V_{CC} = 4.5 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 23.82 \, \text{mA}$
- (3)  $V_{CC} = 5.0 \text{ V}$ ;  $T_{amb} = 25 \,^{\circ}\text{C}$ ;  $I_{CC} = 25.59 \,\text{mA}$
- (4)  $V_{CC} = 5.5 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 27.33 \,\text{mA}$
- (5)  $V_{CC} = 5.5 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 29.30 \,\text{mA}$

Fig 7. Input return loss as function of frequency; typical values

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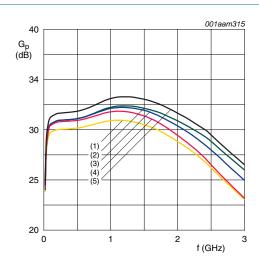
#### **MMIC** wideband amplifier



 $P_{drive} = -40 \text{ dBm}$ ;  $Z_0 = 50 \Omega$ .

- (1)  $V_{CC} = 4.5 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 21.70 \,\text{mA}$
- (2)  $V_{CC} = 4.5 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 23.82 \,\text{mA}$
- (3)  $V_{CC} = 5.0 \text{ V}$ ;  $T_{amb} = 25 \,^{\circ}\text{C}$ ;  $I_{CC} = 25.59 \,\text{mA}$
- (4)  $V_{CC} = 5.5 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 27.33 \,\text{mA}$
- (5)  $V_{CC}$  = 5.5 V;  $T_{amb}$  = -40 °C;  $I_{CC}$  = 29.30 mA

Fig 8. Output return loss as function of frequency; typical values



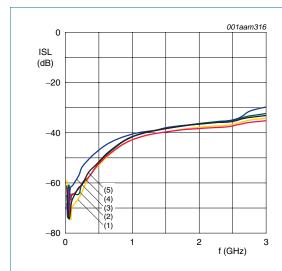
 $P_{drive} = -40 dBm; Z_0 = 50 \Omega.$ 

- (1)  $V_{CC} = 4.5 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 21.70 \,\text{mA}$
- (2)  $V_{CC} = 4.5 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 23.82 \, \text{mA}$
- (3)  $V_{CC} = 5.0 \text{ V}$ ;  $T_{amb} = 25 \,^{\circ}\text{C}$ ;  $I_{CC} = 25.59 \,\text{mA}$
- (4)  $V_{CC} = 5.5 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 27.33 \,\text{mA}$
- (5)  $V_{CC} = 5.5 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 29.30 \,\text{mA}$

Fig 9. Insertion power gain as function of frequency; typical values

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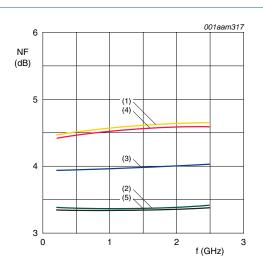
#### **MMIC** wideband amplifier



 $P_{drive} = -40 \text{ dBm}$ ;  $Z_0 = 50 \Omega$ .

- (1)  $V_{CC} = 4.5 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 21.70 \,\text{mA}$
- (2)  $V_{CC} = 4.5 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 23.82 \,\text{mA}$
- (3)  $V_{CC} = 5.0 \text{ V}$ ;  $T_{amb} = 25 \,^{\circ}\text{C}$ ;  $I_{CC} = 25.59 \,\text{mA}$
- (4)  $V_{CC} = 5.5 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 27.33 \,\text{mA}$
- (5)  $V_{CC} = 5.5 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 29.30 \,\text{mA}$

Fig 10. Isolation as function of frequency; typical values



 $Z_0 = 50 \Omega$ .

- (1)  $V_{CC} = 4.5 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 21.70 \,\text{mA}$
- (2)  $V_{CC} = 4.5 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 23.82 \, \text{mA}$
- (3)  $V_{CC} = 5.0 \text{ V}$ ;  $T_{amb} = 25 \,^{\circ}\text{C}$ ;  $I_{CC} = 25.59 \,\text{mA}$
- (4)  $V_{CC} = 5.5 \text{ V}$ ;  $T_{amb} = 85 \,^{\circ}\text{C}$ ;  $I_{CC} = 27.33 \,\text{mA}$
- (5)  $V_{CC} = 5.5 \text{ V}$ ;  $T_{amb} = -40 \,^{\circ}\text{C}$ ;  $I_{CC} = 29.30 \,\text{mA}$

Fig 11. Noise figure as function of frequency; typical values

### 8.3 Tables

Table 7. Supply current over temperature and supply voltages Typical values.

Symbol	Parameter	Conditions	T <sub>amb</sub> (°0	T <sub>amb</sub> (°C)		Unit
			-40	25	85	
I <sub>CC</sub> supply current		$V_{CC} = 4.5 \text{ V}$	23.82	23.00	21.70	mA
		$V_{CC} = 5.0 \text{ V}$	26.65	25.59	24.42	mA
		$V_{CC} = 5.5 \text{ V}$	29.30	27.94	27.33	mA

Table 8. Second harmonic output power over temperature and supply voltages Typical values.

Symbol	Parameter	Conditions	Tamb	(°C)		Unit
			<b>-40</b>	25	85	
$P_{L(2H)}$	second harmonic output power	$f = 250 \text{ MHz}$ ; $P_{drive} = -37 \text{ dBm}$				
		$V_{CC} = 4.5 \text{ V}$	-49	-51	-52	dBm
		$V_{CC} = 5.0 \text{ V}$	-49	-50	-51	dBm
		V <sub>CC</sub> = 5.5 V	-49	-50	-50	dBm
		$f = 950 \text{ MHz}; P_{drive} = -37 \text{ dBm}$				
		V <sub>CC</sub> = 4.5 V	-40	-42	-44	dBm
		V <sub>CC</sub> = 5.0 V	-40	-42	-43	dBm
		V <sub>CC</sub> = 5.5 V	-40	-42	-43	dBm

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Table 9. Input power at 1 dB gain compression over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T <sub>amb</sub> (	°C)		Unit
			-40	25	85	
$P_{i(1dB)} \\$	input power at 1 dB gain compression	f = 250 MHz				
		$V_{CC} = 4.5 \text{ V}$	-21.6	-21.6	-21.6	dBm
		V <sub>CC</sub> = 5.0 V	-21.0	-21.1	-21.1	dBm
		$V_{CC} = 5.5 \text{ V}$	-20.6	-20.7	-20.7	dBm
		f = 950 MHz				
		V <sub>CC</sub> = 4.5 V	-22.7	-22.9	-23.1	dBm
		$V_{CC} = 5.0 \text{ V}$	-22.4	-22.6	-23.0	dBm
		V <sub>CC</sub> = 5.5 V	-22.1	-22.4	-22.9	dBm
		f = 2150 MHz				
		$V_{CC} = 4.5 \text{ V}$	-25.0	-25.6	-26.4	dBm
		V <sub>CC</sub> = 5.0 V	-25.1	-25.9	-26.7	dBm
		V <sub>CC</sub> = 5.5 V	-25.2	-26.2	-27.0	dBm

Table 10. Output power at 1 dB gain compression over temperature and supply voltages *Typical values*.

Symbol Parameter C		Conditions	T <sub>amb</sub> (°C)			Unit
			<b>-40</b>	25	85	
$P_{L(1dB)}$	output power at 1 dB gain compression	f = 250 MHz				
		$V_{CC} = 4.5 \text{ V}$	8.3	7.8	7.3	dBm
	$V_{CC} = 5.0 \text{ V}$	9.3	8.8	8.3	dBm	
	V <sub>CC</sub> = 5.5 V	10.1	9.6	9.0	dBm	
		f = 950 MHz				
		$V_{CC} = 4.5 \text{ V}$	8.0	7.3	6.3	dBm
		$V_{CC} = 5.0 \text{ V}$	8.9	8.0	6.9	dBm
		$V_{CC} = 5.5 V$	9.6	8.6	7.4	dBm
		f = 2150 MHz				
		$V_{CC} = 4.5 \text{ V}$	4.1	2.4	0.3	dBm
		V <sub>CC</sub> = 5.0 V	4.5	2.6	0.2	dBm
		$V_{CC} = 5.5 \text{ V}$	4.7	2.4	0.1	dBm

Table 11. Saturated output power over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T <sub>amb</sub> (	T <sub>amb</sub> (°C)			
			-40	25	85		
P <sub>L(sat)</sub>	saturated output power	f = 250 MHz			'		
		V <sub>CC</sub> = 4.5 V	10.5	10.1	9.6	dBm	
		$V_{CC} = 5.0 \text{ V}$	11.8	11.3	10.8	dBm	
		$V_{CC} = 5.5 \text{ V}$	12.3	11.8	11.3	dBm	
	f = 950 MHz						
		V <sub>CC</sub> = 4.5 V	9.6	8.8	7.7	dBm	
		$V_{CC} = 5.0 \text{ V}$	10.4	9.3	8.2	dBm	
		$V_{CC} = 5.5 \text{ V}$	10.9	9.8	8.5	dBm	
		f = 2150 MHz					
		V <sub>CC</sub> = 4.5 V	5.3	3.7	2.0	dBm	
		V <sub>CC</sub> = 5.0 V	5.7	4.0	2.0	dBm	
		$V_{CC} = 5.5 \text{ V}$	5.9	4.0	2.0	dBm	

Table 12. Second-order intermodulation distance over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T <sub>aml</sub>	, (°C 25	) 85	Unit
ΔΙΜ2	second-order intermodulation distance	$f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$				
		$V_{CC} = 4.5 \text{ V}$	50	48	45	dBc
		$V_{CC} = 5.0 \text{ V}$	51	48	46	dBc
		$V_{CC} = 5.5 \text{ V}$	51	48	46	dBc
		$f_1 = 950 \text{ MHz};$ $f_2 = 951 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$				
		$V_{CC} = 4.5 \text{ V}$	41	40	37	dBc
		$V_{CC} = 5.0 \text{ V}$	42	39	36	dBc
		$V_{CC} = 5.5 \text{ V}$	41	38	35	dBc

Table 13. Output third-order intercept point over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T <sub>amb</sub>	T <sub>amb</sub> (°C)		
			-40	25	85	
IP3 <sub>O</sub>	output third-order intercept point	$f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$				
		V <sub>CC</sub> = 4.5 V	20.8	19.2	18.1	dBm
		V <sub>CC</sub> = 5.0 V	21.6	21.2	20.1	dBm
		V <sub>CC</sub> = 5.5 V	23.3	21.0	20.5	dBm
		$f_1 = 950 \text{ MHz};$ $f_2 = 951 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$				
		$V_{CC} = 4.5 \text{ V}$	20.7	18.9	16.9	dBm
		V <sub>CC</sub> = 5.0 V	21.3	19.4	17.4	dBm
		V <sub>CC</sub> = 5.5 V	21.7	19.9	17.9	dBm
		$f_1 = 2150 \text{ MHz};$ $f_2 = 2151 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$				
		V <sub>CC</sub> = 4.5 V	12.6	10.5	8.2	dBm
		V <sub>CC</sub> = 5.0 V	12.9	10.8	8.4	dBm
		V <sub>CC</sub> = 5.5 V	13.3	10.9	8.5	dBm

Table 14. –3 dB bandwidth over temperature and supply voltages *Typical values*.

Symbol	Parameter	Conditions	T <sub>amb</sub> (°0	T <sub>amb</sub> (°C)		
			-40	25	85	
B <sub>-3dB</sub>	-3 dB bandwidth	$V_{CC} = 4.5 \text{ V}$	2.419	2.312	2.200	GHz
		$V_{CC} = 5.0 \text{ V}$	2.403	2.284	2.164	GHz
		$V_{CC} = 5.5 \text{ V}$	2.378	2.253	2.127	GHz

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### 9. Test information

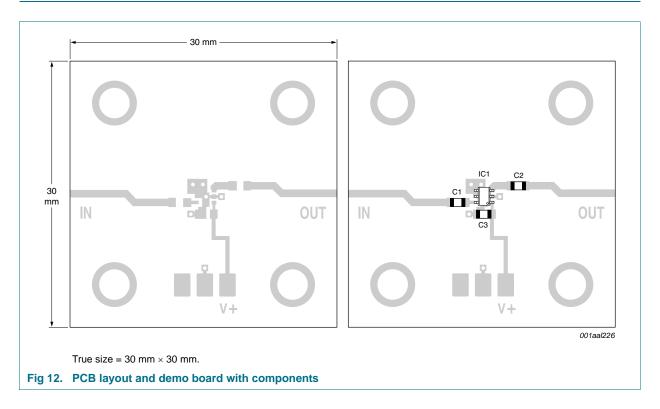


Table 15. List of components used for the typical application

Component	Description	Value	Dimensions
C1, C2	multilayer ceramic chip capacitor	100 pF	0603
C3	multilayer ceramic chip capacitor	22 nF	0603
IC1	BGA2865 MMIC		SOT363

## 10. Package outline

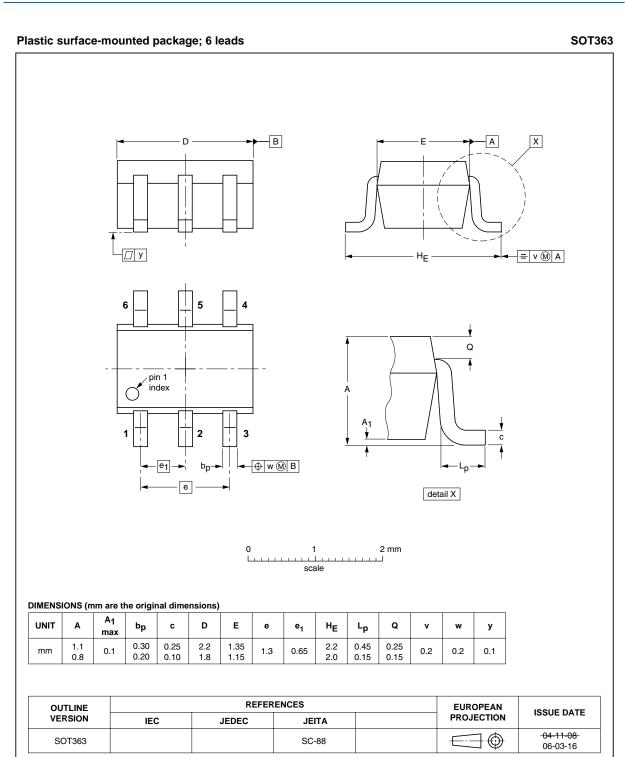


Fig 13. Package outline SOT363

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#### **MMIC** wideband amplifier

### 11. Abbreviations

Table 16. Abbreviations

Acronym	Description
DC	Direct Current
IF	Intermediate Frequency
LNA	Low-Noise Amplifier
LNB	Low-Noise Block converter
PCB	Printed-Circuit Board
RF	Radio Frequency

## 12. Revision history

#### Table 17. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BGA2865 v.2	20101101	Product data sheet	-	BGA2865 v.1	
Modifications	<ul> <li>Table 4 on page 2: The minimum value for V<sub>CC</sub> has been changed to −0.5 V</li> </ul>				
BGA2865 v.1	20100817	Product data sheet	-	-	

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#### **MMIC** wideband amplifier

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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#### MMIC wideband amplifier

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Date of release: 1 November 2010 Document identifier: BGA2865